

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

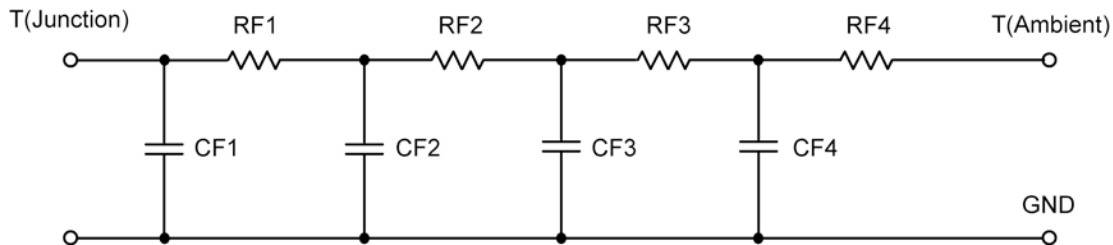
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	14.7844	N/A	7.0563
RT2	5.5708	N/A	1.4543
RT3	19.9741	N/A	2.8867
RT4	44.4130	N/A	13.6027
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	28.9676 m	N/A	5.9640 m
CT2	2.0345 m	N/A	387.3306 u
CT3	123.3055 m	N/A	716.4164 m
CT4	1.4534	N/A	51.9075 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	5.5766	N/A	2.8147
RF2	19.7812	N/A	9.4510
RF3	19.2375	N/A	7.3407
RF4	40.4047	N/A	5.3936
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.5663 m	N/A	770.0395 u
CF2	18.1329 m	N/A	7.5960 m
CF3	114.0489 m	N/A	56.3411 m
CF4	1.4831	N/A	38.4668 m

Note: NA indicates not applicable

## Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

